



Contribution ID: 3

Type: **not specified**

TCAD simulations for silicon sensors and testbeams

Tuesday, 20 January 2015 15:45 (25 minutes)

After a brief introduction of TCAD simulations for silicon sensors, I will present the possibilities offered by combining this kind of simulations together with testbeam data. In particular I will focus on measurements and simulations concerning highly irradiated silicon sensors and I will show how to extract information about the trapping constant and the electric field profile.

Estimated length in minutes

25

Primary author: BOMBEN, Marco (LPNHE)

Presenter: BOMBEN, Marco (LPNHE)

Session Classification: Simulation tools and alike